Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A ~~manufacturing~~ method for manufacturing a substrate used for a liquid crystal device by slant vacuum deposition ~~oblique evaporation~~ of an inorganic material on an underlayer having a gap section on ~~the surface~~a surface formed on the substrate so as to ~~form the~~form an inorganic alignment ~~layers, comprising the steps of:~~layer, comprising:

a first ~~oblique evaporation step by unidirectional oblique evaporation of~~slant vacuum deposition step of disposing the inorganic material unidirectionally on ~~the substrate on which~~ the underlayer having the gap section ~~is formed on the surface of~~formed on the substrate so as to form ~~the first~~a first inorganic ~~oblique evaporation layer 36a;~~slant vacuum deposition layer;

a second ~~oblique evaporation~~slant vacuum deposition step ~~by oblique evaporation of~~of disposing the inorganic material on the substrate unidirectionally, a direction in the second slant vacuum deposition step having an ~~from at least a different~~ azimuth angle ~~inside the substrate from the oblique evaporation direction of the inorganic material in the first oblique evaporation step~~different from at least an azimuth angle of the first slant vacuum deposition step so as to form ~~the second oblique evaporation layer 36b in an area close to~~a second inorganic slant vacuum deposition layer near the gap section and on the first inorganic ~~oblique evaporation layer.~~slant vacuum deposition layer, wherein the direction for disposing the inorganic material unidirectionally in the first or the second slant vacuum deposition step is along a longitudinal direction of the gap section.

2. (Currently Amended) ~~A manufacturing~~The method for manufacturing ~~a substrate~~the substrate used for ~~a~~ the liquid crystal ~~device,~~device according to claim 1, ~~wherein~~

the azimuth angle of the ~~oblique evaporation direction (S_A) of~~ the ~~inorganic material in~~first slant vacuum deposition ~~the first oblique evaporation~~ step and the azimuth angle of ~~the oblique evaporation direction (S_B) of the inorganic material in~~ the second ~~oblique evaporation step differ~~slant vacuum deposition step differing by nearly 90 degrees.

3. (Currently Amended) ~~A manufacturing~~The method of ~~a substrate~~manufacturing the substrate used for ~~a~~ the liquid crystal device according to claim 1, ~~wherein:~~

~~deposition~~ a deposition angle (θ_1) between the ~~oblique evaporation~~ direction ~~of the~~for disposing the inorganic material in the first ~~oblique evaporation~~ slant vacuum deposition step and the substrate ~~is in~~being in the range of 5 to 10 degrees;

~~deposition~~ a deposition angle (θ_2) between the ~~oblique evaporation~~ direction ~~of the~~for disposing the inorganic material in the second ~~oblique evaporation~~slant vacuum deposition step and the substrate ~~is in~~being in the range of 25 to 30 degrees.

4. (Currently Amended) ~~A manufacturing~~The method ~~for a~~of manufacturing the substrate used for ~~a~~ the liquid crystal ~~device,~~device according to claim 1, ~~wherein the~~ a slant vacuum deposition ~~oblique evaporation~~ direction ~~(S_A, S_B) is~~being selected according to a construction and disposition of the gap ~~section (80)~~section formed on ~~the surface~~a surface of the underlayer ~~in the oblique evaporation of inorganic material~~ in at least one of the first ~~oblique evaporation~~slant vacuum deposition step and the second ~~oblique evaporation~~slant vacuum deposition step.

5. (Currently Amended) ~~A manufacturing~~The method of manufacturing ~~for a~~ the substrate used for ~~a~~ the liquid crystal ~~device,~~device according to claim 1, ~~wherein:~~

the thickness of ~~the inorganic~~ the first inorganic slant vacuum deposition ~~oblique evaporation~~ layer formed in the first ~~oblique evaporation~~slant vacuum deposition step is in the range of 5 nm to 16 nm; and

the thickness of the second inorganic slant vacuum deposition ~~the inorganic oblique evaporation~~ layer formed in the second ~~oblique evaporation~~slant vacuum deposition step is in the range of 10 nm to 40 nm.

6. (Currently Amended) ~~A manufacturing~~The method ~~for a substrate~~of manufacturing the substrate used for ~~a~~ the liquid crystal ~~device,~~device according to claim 1, ~~wherein~~ the inorganic material ~~is silicon~~being silicon oxide.